# IS62WV25616ALL
# IS62WV25616BLL

## 256K x 16 LOW VOLTAGE, ULTRA LOW POWER CMOS STATIC SRAM

**AUGUST 2014**

### FEATURES

- High-speed access time: 55ns, 70ns
- CMOS low power operation
  36 mW (typical) operating
  9 µW (typical) CMOS standby
- TTL compatible interface levels
- Single power supply
  1.65V--2.2V $V_{DD}$ (IS62WV25616ALL)
  2.5V--3.6V $V_{DD}$ (IS62WV25616BLL)
- Fully static operation: no clock or refresh required
- Three state outputs
- Data control for upper and lower bytes
- Industrial temperature available
- Lead-free available

### DESCRIPTION

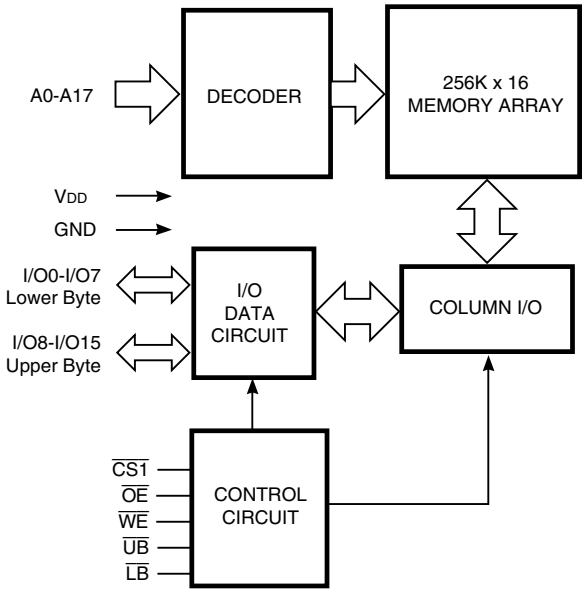
The *ISSI* IS62WV25616ALL/IS62WV25616BLL are high-speed, low power, 4M bit SRAMs organized as 256K words by 16 bits. It is fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When $\overline{CS1}$ is HIGH (deselected) or when $\overline{CS1}$ is LOW and both $\overline{LB}$ and $\overline{UB}$ are HIGH, the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable ($\overline{WE}$) controls both writing and reading of the memory. A data byte allows Upper Byte ($\overline{UB}$) and Lower Byte ($\overline{LB}$) access.

The IS62WV25616ALL/IS62WV25616BLL are packaged in the JEDEC standard 44-Pin TSOP (TYPE II) and 48-pin mini BGA (6mmx8mm).

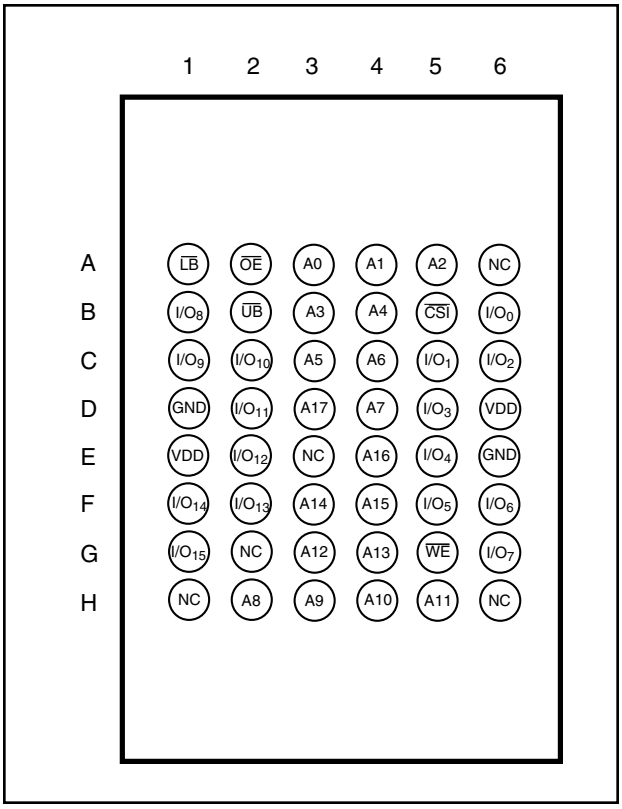
### FUNCTIONAL BLOCK DIAGRAM



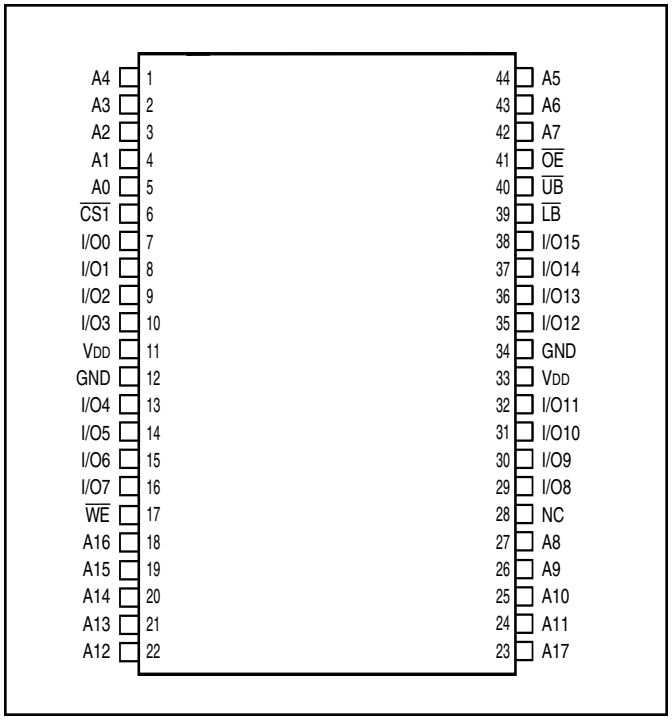

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b.) the user assume all such risks; and
c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

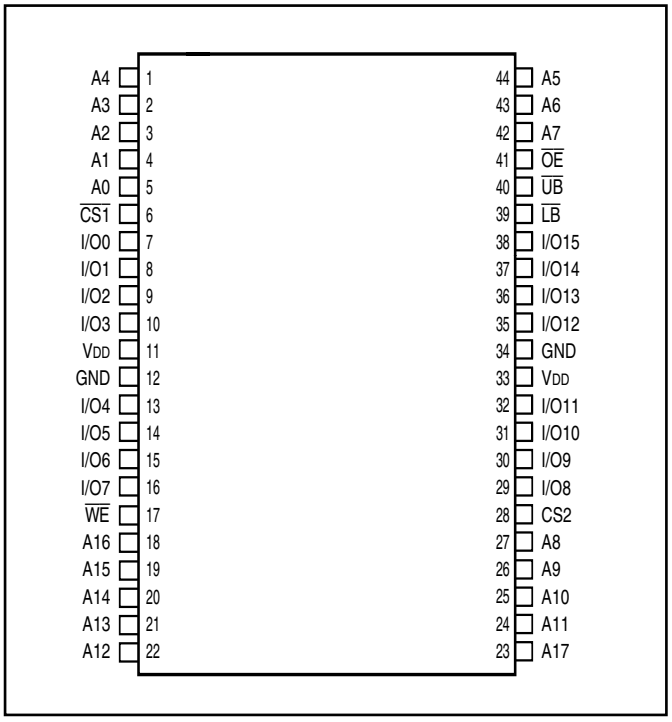
## PIN CONFIGURATIONS
### 48- ball mini BGA (6mm x 8mm) (Package Code B)




### 44-Pin mini TSOP (Type II) (Package Code T)




### 44-Pin mini TSOP (Type II) 2 Chip Enable Option (Package Code T2)




## PIN DESCRIPTIONS

| | |
|---|---|
| A0-A17 | Address Inputs |
| I/O0-I/O15 | Data Inputs/Outputs |
| CS1, CS2 | Chip Enable Input |
| OE | Output Enable Input |
| WE | Write Enable Input |
| LB | Lower-byte Control (I/O0-I/O7) |
| UB | Upper-byte Control (I/O8-I/O15) |
| NC | No Connection |
| VDD | Power |
| GND | Ground |

## TRUTH TABLE

| Mode | $\overline{WE}$ | $\overline{CS1}$ | $\overline{OE}$ | $\overline{LB}$ | $\overline{UB}$ | I/O PIN I/O0-I/O7 | I/O PIN I/O8-I/O15 | $V_{DD}$ Current |
|---|---|---|---|---|---|---|---|---|
| Not Selected | X | H | X | X | X | High-Z | High-Z | $I_{SB1}$, $I_{SB2}$ |
| | X | X | X | H | H | High-Z | High-Z | $I_{SB1}$, $I_{SB2}$ |
| Output Disabled | H | L | H | L | X | High-Z | High-Z | $I_{CC}$ |
| | H | L | H | X | L | High-Z | High-Z | $I_{CC}$ |
| Read | H | L | L | L | H | $D_{OUT}$ | High-Z | $I_{CC}$ |
| | H | L | L | H | L | High-Z | $D_{OUT}$ | |
| | H | L | L | L | L | $D_{OUT}$ | $D_{OUT}$ | |
| Write | L | L | X | L | H | $D_{IN}$ | High-Z | $I_{CC}$ |
| | L | L | X | H | L | High-Z | $D_{IN}$ | |
| | L | L | X | L | L | $D_{IN}$ | $D_{IN}$ | |

## ABSOLUTE MAXIMUM RATINGS(1)

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $V_{TERM}$ | Terminal Voltage with Respect to GND | –0.2 to $V_{DD}$+0.3 | V |
| $V_{DD}$ | $V_{DD}$ Related to GND | –0.2 to $V_{DD}$+0.3 | V |
| $T_{STG}$ | Storage Temperature | –65 to +150 | °C |
| $P_T$ | Power Dissipation | 1.0 | W |

**Note:**

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## OPERATING RANGE ($V_{DD}$)

| Range | Ambient Temperature | IS62WV25616ALL | IS62WV25616BLL |
|---|---|---|---|
| Commercial | 0°C to +70°C | 1.65V - 2.2V | 2.5V-3.6V |
| Industrial | –40°C to +85°C | 1.65V - 2.2V | 2.5V-3.6V |

## DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | Test Conditions | $V_{DD}$ | Min. | Max. | Unit |
|---|---|---|---|---|---|---|
| $V_{OH}$ | Output HIGH Voltage | $I_{OH}$ = -0.1 mA | 1.65-2.2V | 1.4 | — | V |
| | | $I_{OH}$ = -1 mA | 2.5-3.6V | 2.2 | — | V |
| $V_{OL}$ | Output LOW Voltage | $I_{OL}$ = 0.1 mA | 1.65-2.2V | — | 0.2 | V |
| | | $I_{OL}$ = 2.1 mA | 2.5-3.6V | — | 0.4 | V |
| $V_{IH}$ | Input HIGH Voltage | | 1.65-2.2V | 1.4 | $V_{DD}$ + 0.2 | V |
| | | | 2.5-3.6V | 2.2 | $V_{DD}$ + 0.3 | V |
| $V_{IL}$(1) | Input LOW Voltage | | 1.65-2.2V | –0.2 | 0.4 | V |
| | | | 2.5-3.6V | –0.2 | 0.8 | V |
| $I_{LI}$ | Input Leakage | GND ≤ $V_{IN}$ ≤ $V_{DD}$ | | –1 | 1 | µA |
| $I_{LO}$ | Output Leakage | GND ≤ $V_{OUT}$ ≤ $V_{DD}$, Outputs Disabled | | –1 | 1 | µA |

**Notes:** 1. $V_{IL}$ (min.) = –1.0V for pulse width less than 10 ns.

## IS62WV25616ALL, POWER SUPPLY CHARACTERISTICS[1] (Over Operating Range)

| Symbol | Parameter | Test Conditions | | Max. 70 | Unit |
|---|---|---|---|---|---|
| $I_{CC}$ | $V_{DD}$ Dynamic Operating Supply Current | $V_{DD}$ = Max., $I_{OUT}$ = 0 mA, f = $f_{MAX}$ | Com.<br>Ind. | 25<br>30 | mA |
| $I_{CC1}$ | Operating Supply Current | $V_{DD}$ = Max., $\overline{CS1}$ = 0.2V<br>$\overline{WE}$ = $V_{DD}$-0.2V<br>f=1MHZ | Com.<br>Ind. | 10<br>10 | mA |
| $I_{SB1}$ | TTL Standby Current (TTL Inputs) | $V_{DD}$ = Max., $V_{IN}$ = $V_{IH}$ or $V_{IL}$<br>$\overline{CS1}$ = $V_{IH}$ , f = 1 MHz<br>**OR** | Com.<br>Ind. | 0.35<br>0.35 | mA |
| | ULB Control | $V_{DD}$ = Max., $V_{IN}$ = $V_{IH}$ or $V_{IL}$<br>$\overline{CS1}$ = $V_{IL}$, f = 0, $\overline{UB}$ = $V_{IH}$, $\overline{LB}$ = $V_{IH}$ | | | |
| $I_{SB2}$ | CMOS Standby Current (CMOS Inputs) | $V_{DD}$ = Max., $\overline{CS1}$ ≥ $V_{DD}$ – 0.2V, $V_{IN}$ ≥ $V_{DD}$ – 0.2V, or $V_{IN}$ ≤ 0.2V, f = 0<br>**OR** | Com.<br>Ind. | 15<br>15 | µA |
| | ULB Control | $V_{DD}$ = Max., $\overline{CS1}$ = $V_{IL}$, $V_{IN}$ ≤ 0.2V, f = 0; $\overline{UB}$ / $\overline{LB}$ = $V_{DD}$ – 0.2V | | | |

## IS62WV25616BLL, POWER SUPPLY CHARACTERISTICS[1] (Over Operating Range)

| Symbol | Parameter | Test Conditions | | Max. 55 | Max. 70 | Unit |
|---|---|---|---|---|---|---|
| $I_{CC}$ | $V_{DD}$ Dynamic Operating Supply Current | $V_{DD}$ = Max., $I_{OUT}$ = 0 mA, f = $f_{MAX}$ | Com.<br>Ind. | 40<br>45 | 35<br>40 | mA |
| $I_{CC1}$ | Operating Supply Current | $V_{DD}$ = Max., $\overline{CS1}$ = 0.2V<br>$\overline{WE}$ = $V_{DD}$-0.2V<br>f=1MHZ | Com.<br>Ind. | 15<br>15 | 15<br>15 | mA |
| $I_{SB1}$ | TTL Standby Current (TTL Inputs) | $V_{DD}$ = Max., $V_{IN}$ = $V_{IH}$ or $V_{IL}$<br>$\overline{CS1}$ = $V_{IH}$, f = 1 MHz<br>**OR** | Com.<br>Ind. | 0.35<br>0.35 | 0.35<br>0.35 | mA |
| | ULB Control | $V_{DD}$ = Max., $V_{IN}$ = $V_{IH}$ or $V_{IL}$<br>$\overline{CS1}$ = $V_{IL}$, f = 0, $\overline{UB}$ = $V_{IH}$, $\overline{LB}$ = $V_{IH}$ | | | | |
| $I_{SB2}$ | CMOS Standby Current (CMOS Inputs) | $V_{DD}$ = Max., $\overline{CS1}$ ≥ $V_{DD}$ – 0.2V, $V_{IN}$ ≥ $V_{DD}$ – 0.2V, or $V_{IN}$ ≤ 0.2V, f = 0<br>**OR** | Com.<br>Ind.<br>typ.[1] | 15<br>15<br>3 | 15<br>15 | µA |
| | ULB Control | $V_{DD}$ = Max., $\overline{CS1}$ = $V_{IL}$, $V_{IN}$ ≤ 0.2V, f = 0; $\overline{UB}$ / $\overline{LB}$ = $V_{DD}$ – 0.2V | | | | |

Note:

1. Typical values are measured at $V_{DD}$ = 3.0V, $T_A$ = 25°C. Not 100% tested.

## CAPACITANCE[1]

| Symbol | Parameter | Conditions | Max. | Unit |
|---|---|---|---|---|
| $C_{IN}$ | Input Capacitance | $V_{IN}$ = 0V | 8 | pF |
| $C_{OUT}$ | Input/Output Capacitance | $V_{OUT}$ = 0V | 10 | pF |

**Note:**
1. Tested initially and after any design or process changes that may affect these parameters.

## AC TEST CONDITIONS

| Parameter | IS62WV25616ALL (Unit) | IS62WV25616BLL (Unit) |
|---|---|---|
| Input Pulse Level | 0.4V to $V_{DD}$-0.2V | 0.4V to $V_{DD}$-0.3V |
| Input Rise and Fall Times | 5 ns | 5ns |
| Input and Output Timing and Reference Level | $V_{REF}$ | $V_{REF}$ |
| Output Load | See Figures 1 and 2 | See Figures 1 and 2 |

| | IS62WV25616ALL 1.65V-2.2V | IS62WV25616BLL 2.5V - 3.6V |
|---|---|---|
| **R1(Ω)** | 3070 | 3070 |
| **R2(Ω)** | 3150 | 3150 |
| **$V_{REF}$** | 0.9V | 1.5V |
| **$V_{TM}$** | 1.8V | 2.8V |

## AC TEST LOADS

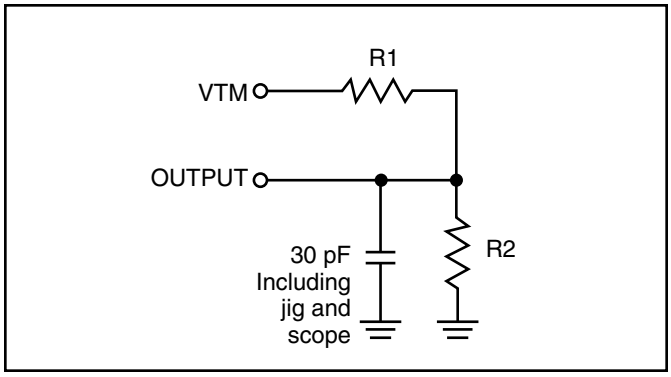



**Figure 1**

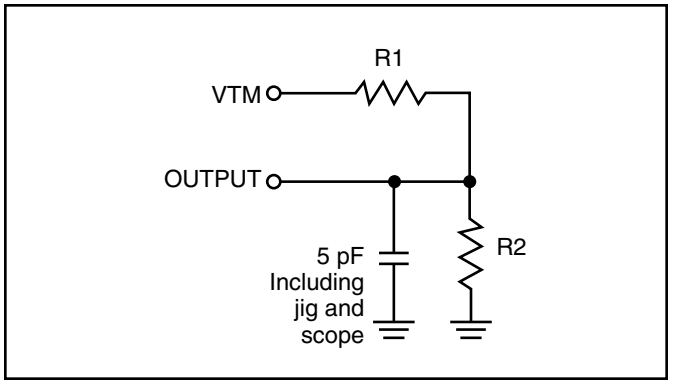



**Figure 2**

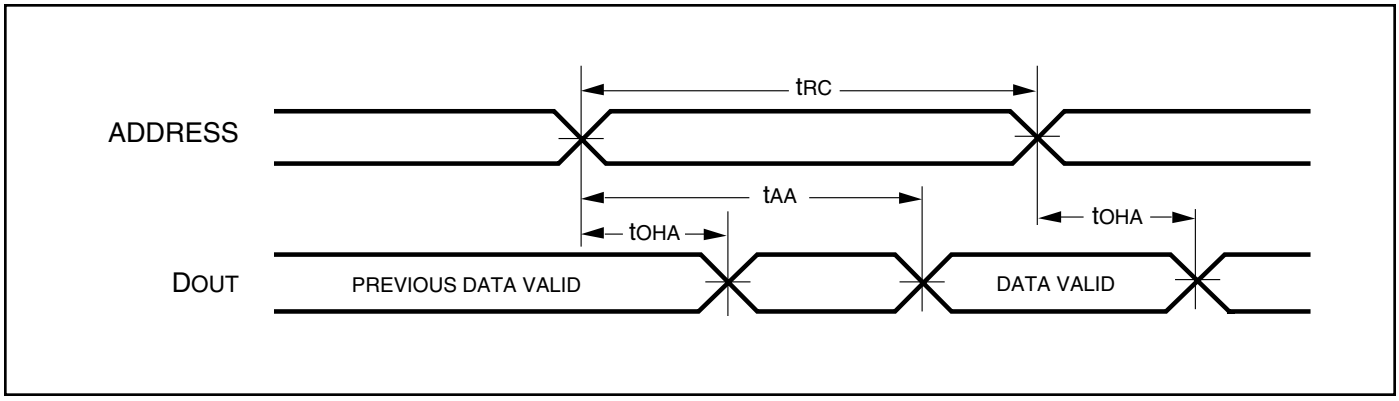
## READ CYCLE SWITCHING CHARACTERISTICS[1] (Over Operating Range)

| Symbol | Parameter | 55 ns Min. | 55 ns Max. | 70 ns Min. | 70 ns Max. | Unit |
|---|---|---|---|---|---|---|
| $t_{RC}$ | Read Cycle Time | 55 | — | 70 | — | ns |
| $t_{AA}$ | Address Access Time | — | 55 | — | 70 | ns |
| $t_{OHA}$ | Output Hold Time | 10 | — | 10 | — | ns |
| $t_{ACS1}$ | $\overline{CS1}$ Access Time | — | 55 | — | 70 | ns |
| $t_{DOE}$ | $\overline{OE}$ Access Time | — | 25 | — | 35 | ns |
| $t_{HZOE}$[2] | $\overline{OE}$ to High-Z Output | — | 20 | — | 25 | ns |
| $t_{LZOE}$[2] | $\overline{OE}$ to Low-Z Output | 5 | — | 5 | — | ns |
| $t_{HZCS1}$ | $\overline{CS1}$ to High-Z Output | 0 | 20 | 0 | 25 | ns |
| $t_{LZCS1}$ | $\overline{CS1}$ to Low-Z Output | 10 | — | 10 | — | ns |
| $t_{BA}$ | $\overline{LB}$, $\overline{UB}$ Access Time | — | 55 | — | 70 | ns |
| $t_{HZB}$ | $\overline{LB}$, $\overline{UB}$ to High-Z Output | 0 | 20 | 0 | 25 | ns |
| $t_{LZB}$ | $\overline{LB}$, $\overline{UB}$ to Low-Z Output | 0 | — | 0 | — | ns |

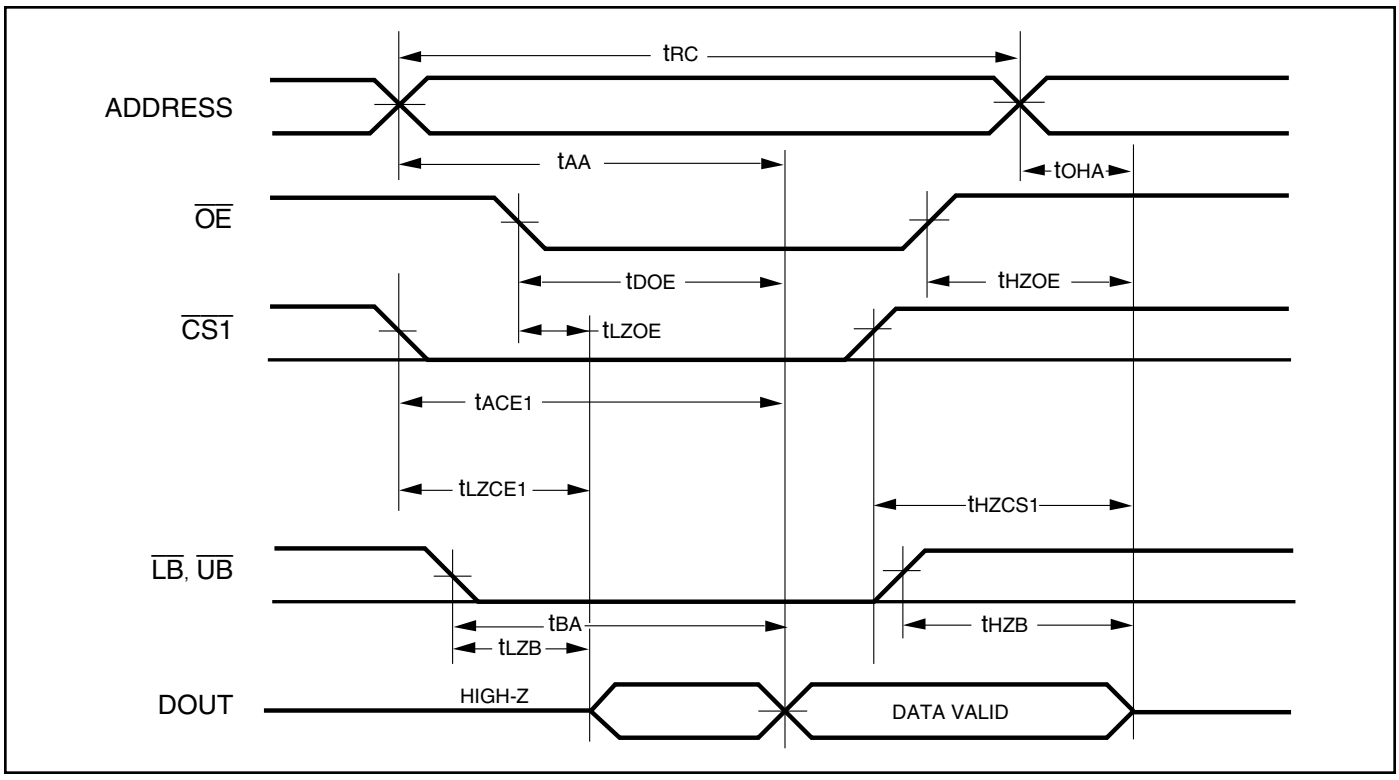
**Notes:**
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to $V_{DD}$-0.2V/$V_{DD}$-0.3V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

## AC WAVEFORMS

### READ CYCLE NO. 1[1,2] (Address Controlled) ($\overline{CS1}$ = $\overline{OE}$ = $V_{IL}$, $\overline{WE}$ = $V_{IH}$, $\overline{UB}$ or $\overline{LB}$ = $V_{IL}$)




### READ CYCLE NO. 2[1,3] ($\overline{CS1}$, $\overline{OE}$, AND $\overline{UB}$/$\overline{LB}$ Controlled)




**Notes:**
1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CS1}$, $\overline{UB}$, or $\overline{LB}$ = $V_{IL}$. $\overline{WE}$=$V_{IH}$.
3. Address is valid prior to or coincident with $\overline{CS1}$ LOW transition.

## WRITE CYCLE SWITCHING CHARACTERISTICS[1,2] (Over Operating Range)

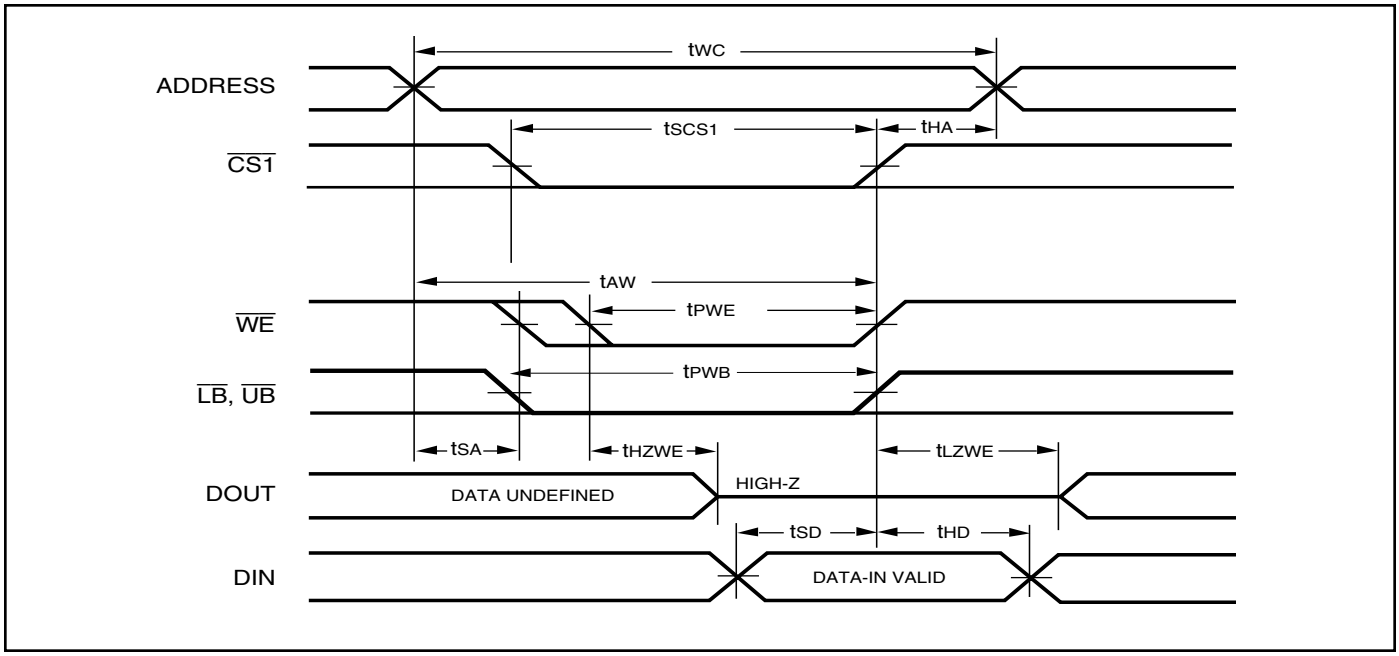
| Symbol | Parameter | 55 ns Min. | 55 ns Max. | 70 ns Min. | 70 ns Max. | Unit |
|---|---|---|---|---|---|---|
| $t_{WC}$ | Write Cycle Time | 55 | — | 70 | — | ns |
| $t_{SCS1}$ | $\overline{CS1}$ to Write End | 45 | — | 60 | — | ns |
| $t_{AW}$ | Address Setup Time to Write End | 45 | — | 60 | — | ns |
| $t_{HA}$ | Address Hold from Write End | 0 | — | 0 | — | ns |
| $t_{SA}$ | Address Setup Time | 0 | — | 0 | — | ns |
| $t_{PWB}$ | $\overline{LB}$, $\overline{UB}$ Valid to End of Write | 45 | — | 60 | — | ns |
| $t_{PWE}$ | $\overline{WE}$ Pulse Width | 40 | — | 50 | — | ns |
| $t_{SD}$ | Data Setup to Write End | 25 | — | 30 | — | ns |
| $t_{HD}$ | Data Hold from Write End | 0 | — | 0 | — | ns |
| $t_{HZWE}$[3] | $\overline{WE}$ LOW to High-Z Output | — | 20 | — | 20 | ns |
| $t_{LZWE}$[3] | $\overline{WE}$ HIGH to Low-Z Output | 5 | — | 5 | — | ns |

**Notes:**

1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to $V_{DD}$-0.2V/$V_{DD}$-0.3V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of $\overline{CS1}$ LOW and $\overline{UB}$ or $\overline{LB}$, and $\overline{WE}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

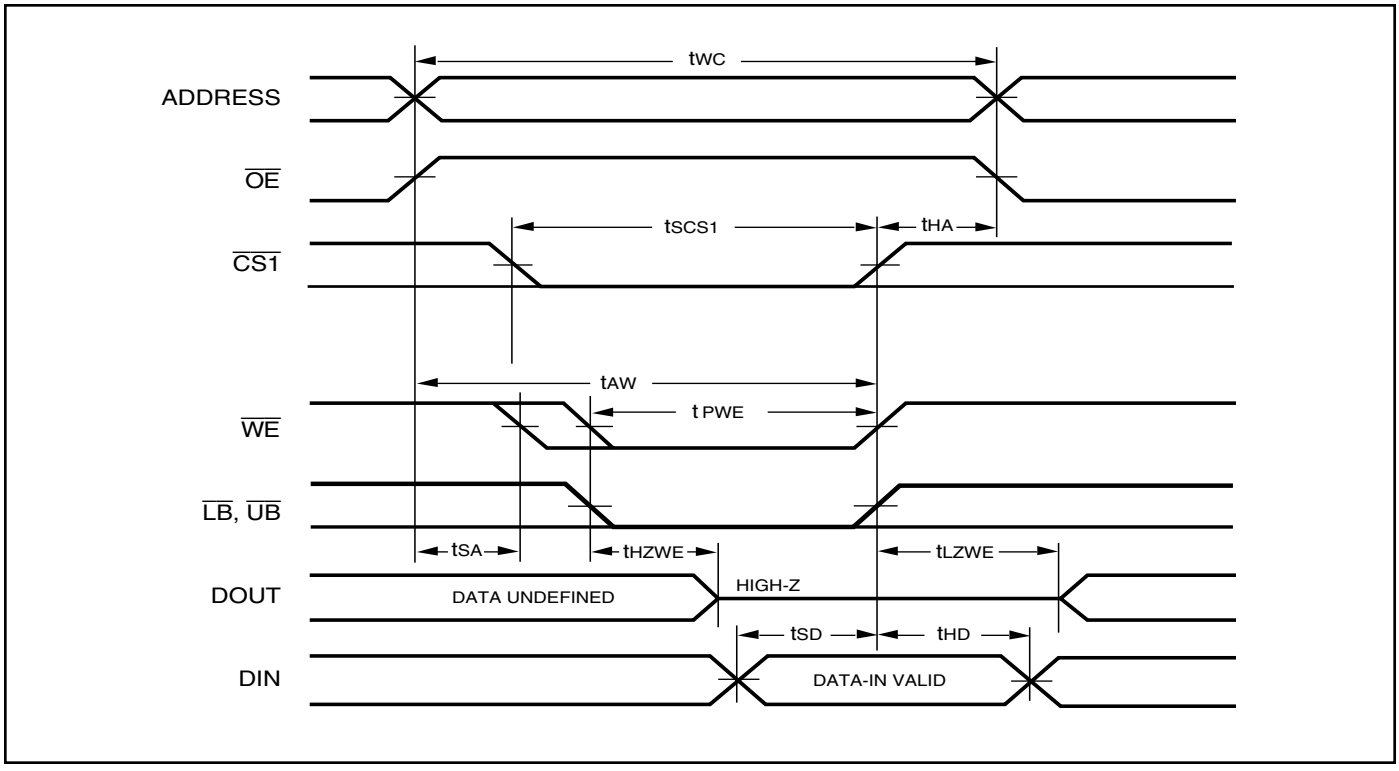
## AC WAVEFORMS

### WRITE CYCLE NO. 1[1,2] ($\overline{CS1}$ Controlled, $\overline{OE}$ = HIGH or LOW)

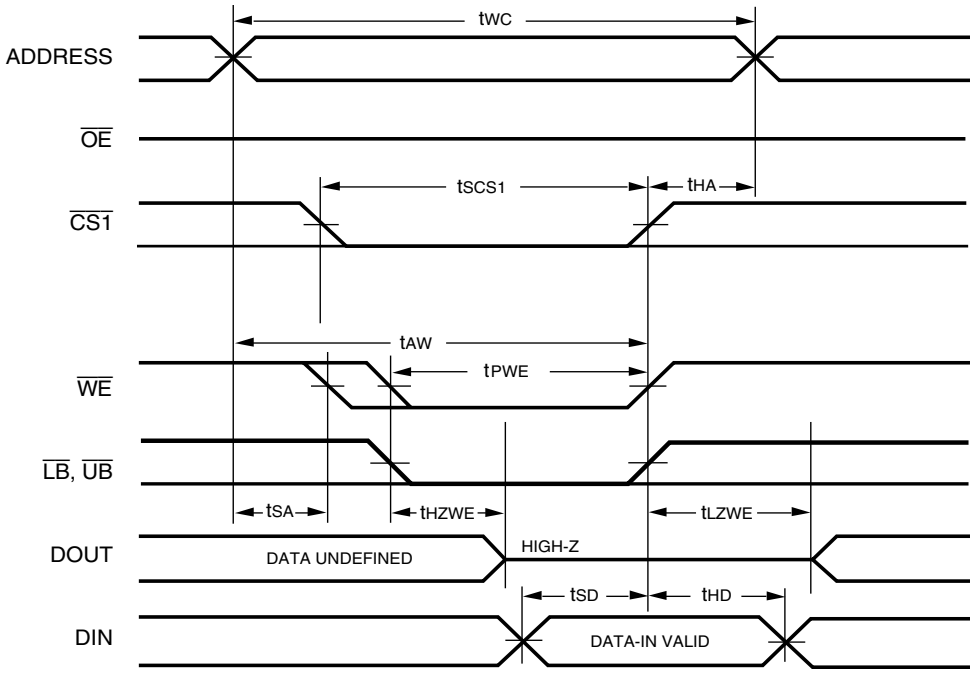



**Notes:**
1. WRITE is an internally generated signal asserted during an overlap of the LOW states on the $\overline{CS1}$ and $\overline{WE}$ inputs and at least one of the $\overline{LB}$ and $\overline{UB}$ inputs being in the LOW state.
2. WRITE = ($\overline{CS1}$) [ ($\overline{LB}$) = ($\overline{UB}$) ] ($\overline{WE}$).

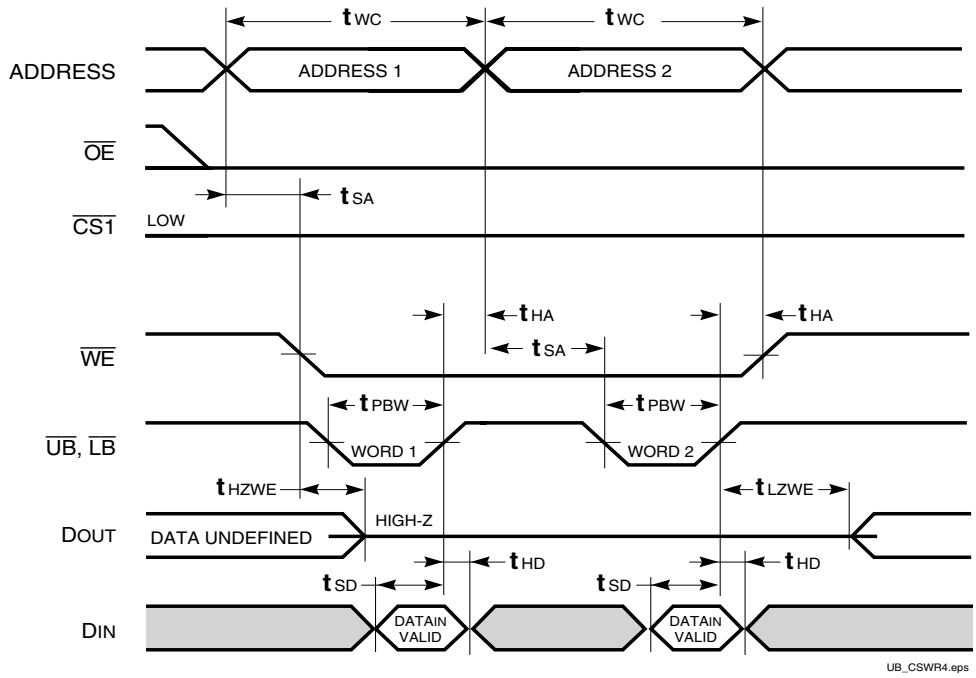
### WRITE CYCLE NO. 2 ($\overline{WE}$ Controlled: $\overline{OE}$ is HIGH During Write Cycle)



## WRITE CYCLE NO. 3 ($\overline{WE}$ Controlled: $\overline{OE}$ is LOW During Write Cycle)



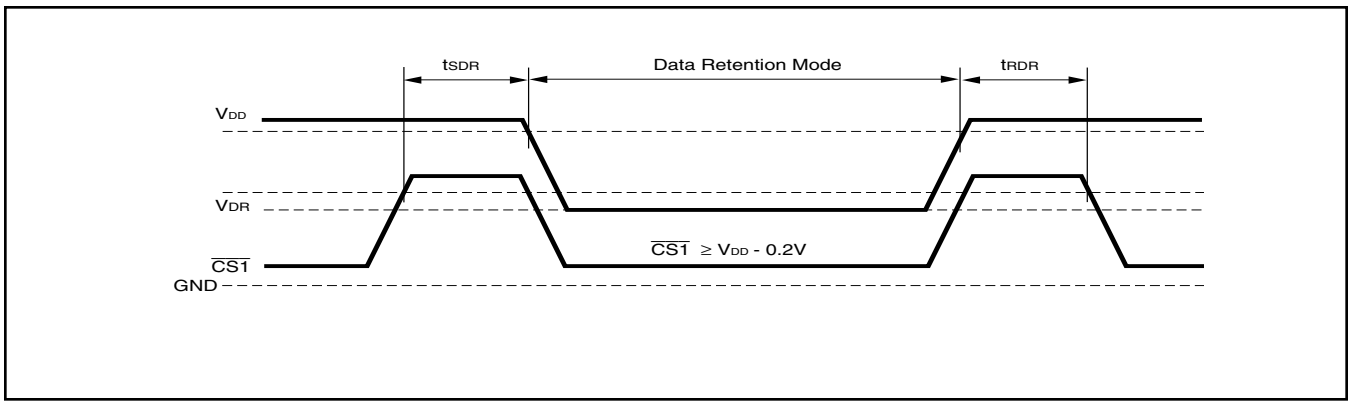

## WRITE CYCLE NO. 4 ($\overline{UB}$/$\overline{LB}$ Controlled)



## DATA RETENTION SWITCHING CHARACTERISTICS

| Symbol | Parameter | Test Condition | Min. | Max. | Unit |
|---|---|---|---|---|---|
| $V_{DR}$ | $V_{DD}$ for Data Retention | See Data Retention Waveform | 1.2 | 3.6 | V |
| $I_{DR}$ | Data Retention Current | $V_{DD}$ = 1.2V, $\overline{CS1} \geq V_{DD} - 0.2V$ | — | 15 | µA |
| $t_{SDR}$ | Data Retention Setup Time | See Data Retention Waveform | 0 | — | ns |
| $t_{RDR}$ | Recovery Time | See Data Retention Waveform | $t_{RC}$ | — | ns |

## DATA RETENTION WAVEFORM ($\overline{CS1}$ Controlled)



## ORDERING INFORMATION

### IS62WV25616ALL (1.65V-2.2V)

#### Commercial Range: 0°C to +70°C

| Speed (ns) | Order Part No. | Package |
|---|---|---|
| 70 | IS62WV25616ALL-70T | TSOP |

#### Industrial Range: –40°C to +85°C

| Speed (ns) | Order Part No. | Package |
|---|---|---|
| 70 | IS62WV25616ALL-70TI | TSOP |
| 70 | IS62WV25616ALL-70BI | mini BGA (6mmx8mm) |
| 70 | IS62WV25616ALL-70BLI | mini BGA (6mmx8mm), Lead-free |

### IS62WV25616BLL (2.5V - 3.6V)

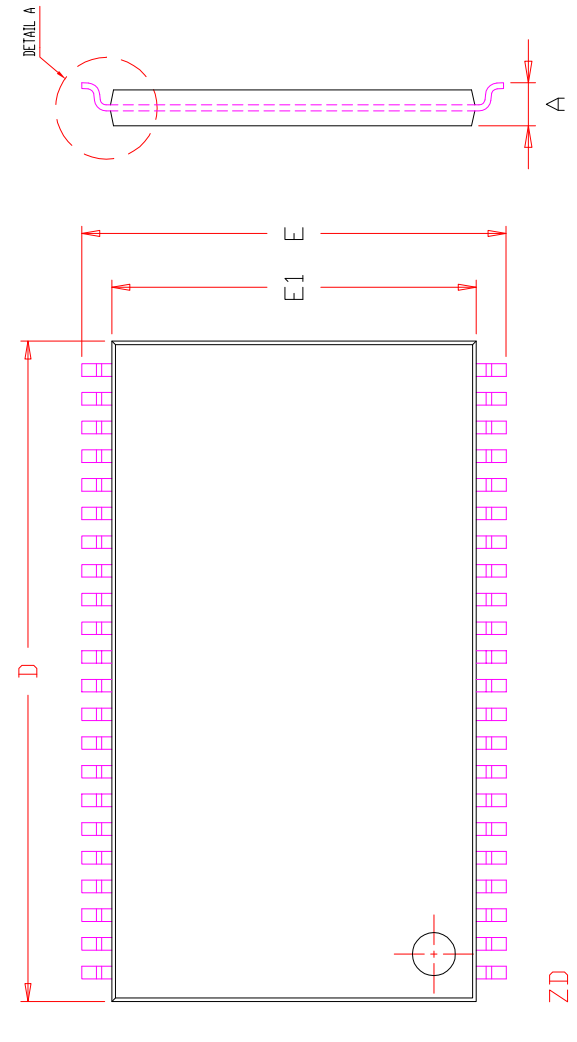
#### Commercial Range: 0°C to +70°C

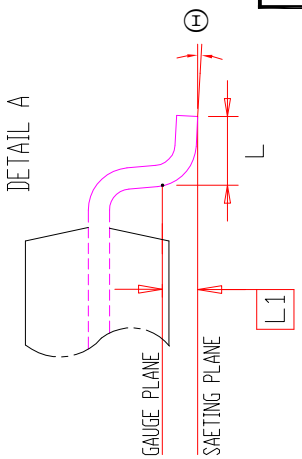
| Speed (ns) | Order Part No. | Package |
|---|---|---|
| 55 | IS62WV25616BLL-55T | TSOP |
| 70 | IS62WV25616BLL-70T | TSOP |

#### Industrial Range: –40°C to +85°C

| Speed (ns) | Order Part No. | Package |
|---|---|---|
| 55 | IS62WV25616BLL-55TI | TSOP |
| 55 | IS62WV25616BLL-55TLI | TSOP, Lead-free |
| 55 | IS62WV25616BLL-55T2LI | TSOP, Lead-free, 2 CS Option |
| 55 | IS62WV25616BLL-55BI | mini BGA (6mmx8mm) |
| 55 | IS62WV25616BLL-55BLI | mini BGA (6mmx8mm), Lead-free |

| SYMBOL | DIMENSION IN MM | | | DIMENSION IN INCH | | |
|---|---|---|---|---|---|---|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 1.00 | — | 1.20 | 0.039 | — | 0.047 |
| A1 | 0.05 | — | 0.15 | 0.002 | — | 0.006 |
| A2 | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 |
| b | 0.30 | — | 0.45 | 0.012 | — | 0.018 |
| D | 18.28 | 18.41 | 18.54 | 0.720 | 0.725 | 0.730 |
| E | 11.56 | 11.76 | 11.96 | 0.455 | 0.463 | 0.471 |
| E1 | 10.03 | 10.16 | 10.29 | 0.395 | 0.400 | 0.405 |
| e | 0.80 BSC. | | | 0.031 BSC. | | |
| L | 0.40 | — | 0.69 | 0.016 | — | 0.027 |
| L1 | 0.25 BSC. | | | 0.010 BSC. | | |
| ZD | 0.805 REF. | | | 0.032 REF. | | |
| θ | 0 | — | 8° | 0 | — | 8° |




NOTE :

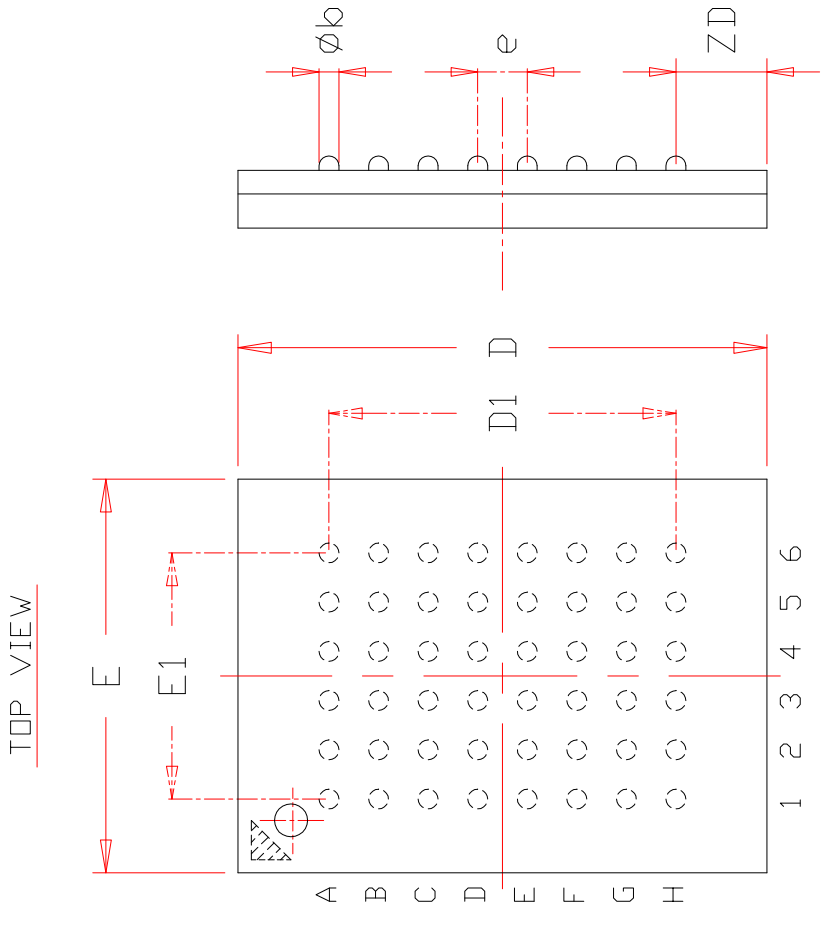
1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.

| | TITLE | REV. | DATE |
|---|---|---|---|
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| SYMBOL | DIMENSION IN MM | | | DIMENSION IN INCH | | |
|---|---|---|---|---|---|---|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | — | — | 1.20 | — | — | 0.047 |
| A1 | 0.20 | — | 0.30 | 0.008 | — | 0.012 |
| øb | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| D | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| D1 | | 5.25 BSC | | | 0.207 BSC | |
| E | 5.90 | 6.00 | 6.10 | 0.232 | 0.236 | 0.240 |
| E1 | | 3.75 BSC | | | 0.148 BSC | |
| e | | 0.75 BSC. | | | 0.030 BSC. | |
| ZD | | 1.375 REF. | | | 0.054 REF. | |
| ZE | | 1.125 REF. | | | 0.044 REF. | |

NOTE :

1. CONTROLLING DIMENSION : MM.
2. Reference document : JEDEC MO-207




| ISSI | TITLE | 48L 6x8mm TF-BGA Package Outline | REV. | C | DATE | 08/12/2008 |
|---|---|---|---|---|---|---|